

## Trench gate field-stop IGBT, H series 600 V, 15 A high speed

Datasheet - production data

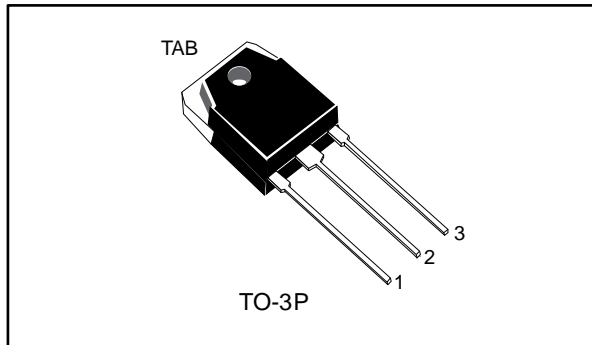
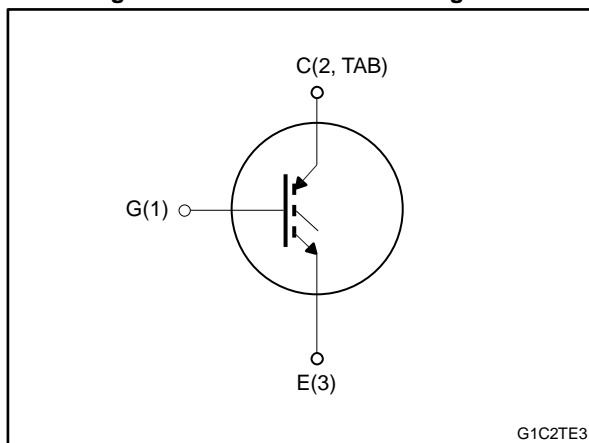


Figure 1: Internal schematic diagram



### Features

- High speed switching
- Tight parameter distribution
- Safe paralleling
- Low thermal resistance
- Short-circuit rated

### Applications

- Motor control
- UPS
- PFC

### Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the H series of IGBTs, which represents an optimum compromise between conduction and switching losses to maximize the efficiency of high switching frequency converters. Furthermore, a slightly positive  $V_{CE(sat)}$  temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Table 1: Device summary

Order code	Marking	Package	Packing
STGWT15H60F	G15H60F	TO-3P	Tube

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# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ V)	600	V
$I_C$	Continuous collector current at $T_C = 25$ °C	30	A
	Continuous collector current at $T_C = 100$ °C	15	
$I_{CP}^{(1)}$	Pulsed collector current	60	A
$V_{GE}$	Gate-emitter voltage	$\pm 20$	V
$P_{TOT}$	Total dissipation at $T_C = 25$ °C	115	W
$T_{STG}$	Storage temperature range	-55 to 150	°C
$T_J$	Operating junction temperature range	-55 to 175	°C

**Notes:**

<sup>(1)</sup>Pulse width is limited by maximum junction temperature.

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thJC}$	Thermal resistance junction-case	1.3	°C/W
$R_{thJA}$	Thermal resistance junction-ambient	50	°C/W

## 2 Electrical characteristics

$T_J = 25\text{ °C}$  unless otherwise specified

**Table 4: Static characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)CES}$	Collector-emitter breakdown voltage	$V_{GE} = 0\text{ V}$ , $I_C = 2\text{ mA}$	600			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}$ , $I_C = 15\text{ A}$		1.6	2	V
		$V_{GE} = 15\text{ V}$ , $I_C = 15\text{ A}$ , $T_J = 125\text{ °C}$		1.7		
		$V_{GE} = 15\text{ V}$ , $I_C = 15\text{ A}$ , $T_J = 175\text{ °C}$		1.8		
$V_{GE(th)}$	Gate threshold voltage	$V_{CE} = V_{GE}$ , $I_C = 1\text{ mA}$	5	6	7	V
$I_{CES}$	Collector cut-off current	$V_{GE} = 0\text{ V}$ , $V_{CE} = 600\text{ V}$			25	$\mu\text{A}$
$I_{GES}$	Gate-emitter leakage current	$V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$			$\pm 250$	nA

**Table 5: Dynamic characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance	$V_{CE} = 25\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GE} = 0\text{ V}$	-	1952	-	pF
$C_{oes}$	Output capacitance		-	78	-	pF
$C_{res}$	Reverse transfer capacitance		-	45	-	pF
$Q_g$	Total gate charge	$V_{CC} = 480\text{ V}$ , $I_C = 15\text{ A}$ , $V_{GE} = 0\text{ to }15\text{ V}$ (see <a href="#">Figure 24: "Gate charge test circuit"</a> )	-	81	-	nC
$Q_{ge}$	Gate-emitter charge		-	8	-	nC
$Q_{gc}$	Gate-collector charge		-	42	-	nC

Table 6: Switching characteristics (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 15\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 10\ \Omega$		24.5	-	ns
$t_r$	Current rise time			8.2	-	ns
$(di/dt)_{on}$	Turn-on current slope			1470	-	A/ $\mu$ s
$t_{d(on)}$	Turn-on delay time	$V_{CE} = 400\text{ V}$ , $I_C = 15\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 10\ \Omega$ , $T_J = 175\text{ }^\circ\text{C}$ (see <a href="#">Figure 23: "Test circuit for inductive load switching"</a> )		25	-	ns
$t_r$	Current rise time			9	-	ns
$(di/dt)_{on}$	Turn-on current slope			1370	-	A/ $\mu$ s
$t_{r(Voff)}$	Off voltage rise time	$V_{CE} = 400\text{ V}$ , $I_C = 15\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 10\ \Omega$		18	-	ns
$t_{d(off)}$	Turn-off delay time			118	-	ns
$t_f$	Current fall time			69	-	ns
$t_{r(Voff)}$	Off voltage rise time	$V_{CE} = 400\text{ V}$ , $I_C = 15\text{ A}$ , $V_{GE} = 15\text{ V}$ , $R_G = 10\ \Omega$ , $T_J = 175\text{ }^\circ\text{C}$ (see <a href="#">Figure 23: "Test circuit for inductive load switching"</a> )		27	-	ns
$t_{d(off)}$	Turn-off delay time			124	-	ns
$t_f$	Current fall time			101	-	ns
$t_{sc}$	Short-circuit withstand time	$V_{CC} \leq 360\text{ V}$ , $V_{GE} = 15\text{ V}$ , $R_G = 10\ \Omega$	3	5	-	$\mu$ s

Table 7: Switching energy (inductive load)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CE} = 400\text{ V}$ , $I_C = 15\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$	-	136	-	$\mu$ J	
$E_{off}^{(2)}$	Turn-off switching energy			-	207	-	$\mu$ J
$E_{ts}$	Total switching energy			-	343	-	$\mu$ J
$E_{on}^{(1)}$	Turn-on switching energy	$V_{CE} = 400\text{ V}$ , $I_C = 15\text{ A}$ , $R_G = 10\ \Omega$ , $V_{GE} = 15\text{ V}$ , $T_J = 175\text{ }^\circ\text{C}$	-	224	-	$\mu$ J	
$E_{off}^{(2)}$	Turn-off switching energy			-	329	-	$\mu$ J
$E_{ts}$	Total switching energy			-	553	-	$\mu$ J

**Notes:**

(1) Including the reverse recovery of the external diode. The diode is the same of the co-packed STGP15H60DF.

(2) Including the tail of the collector current.

2.1 Electrical characteristics (curves)

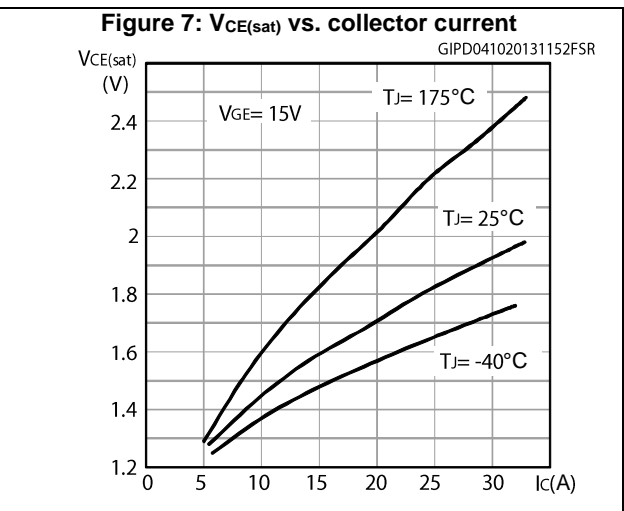
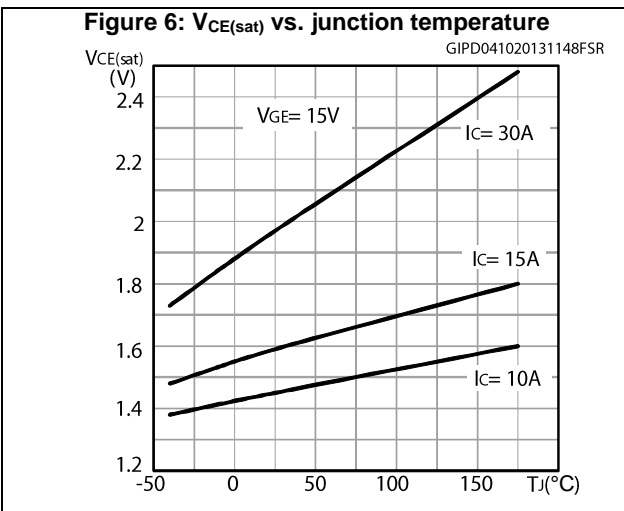
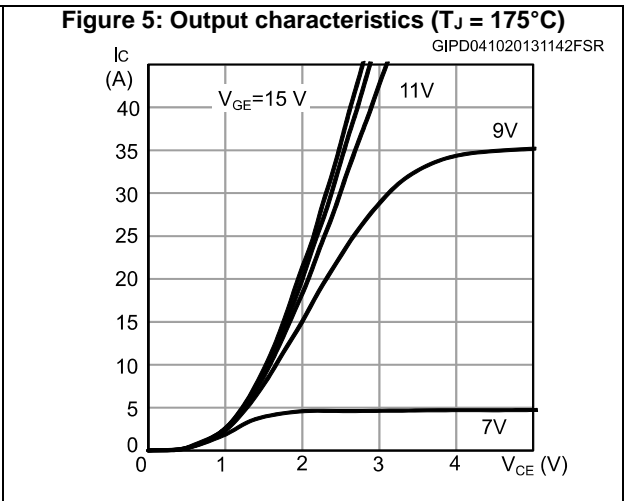
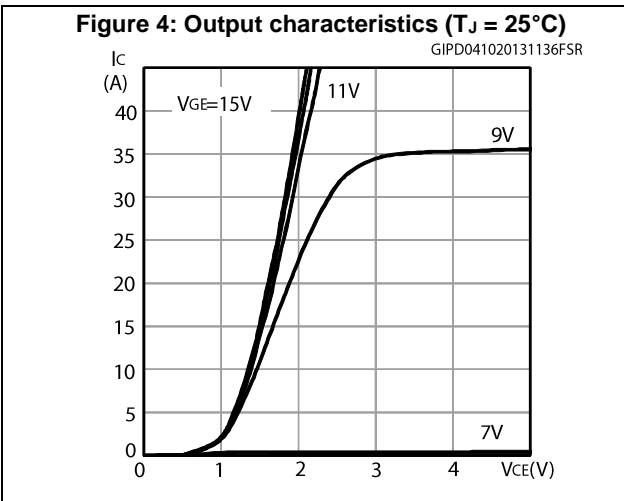
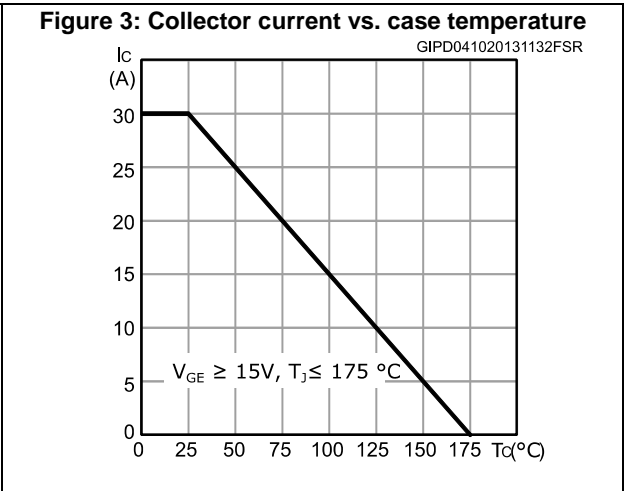
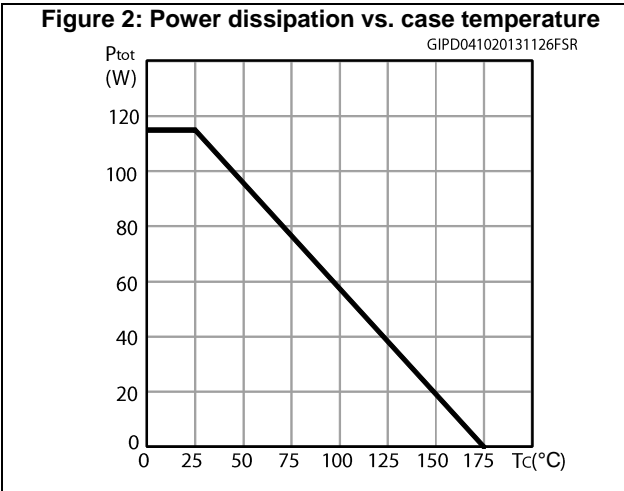


Figure 8: Collector current vs. switching frequency

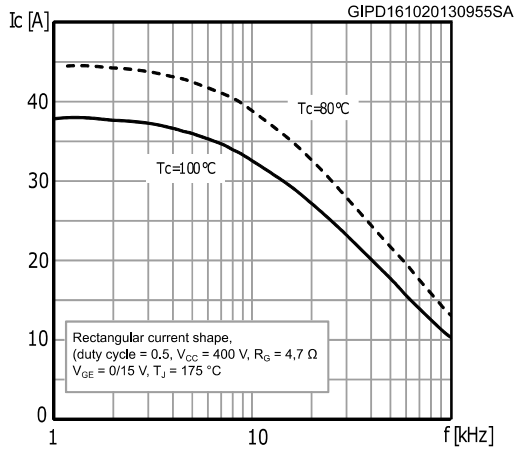


Figure 9: Forward bias safe operating area

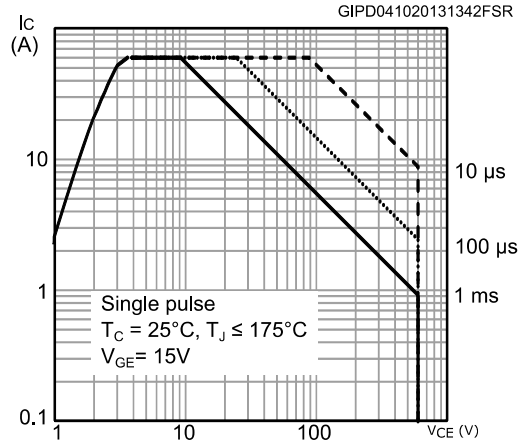


Figure 10: Transfer characteristics

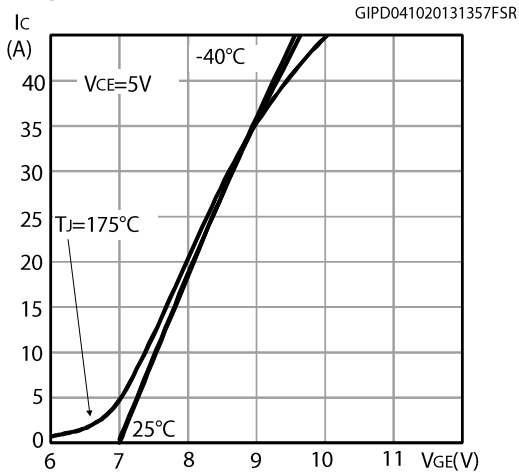


Figure 11: Normalized Vge(th) vs junction temperature

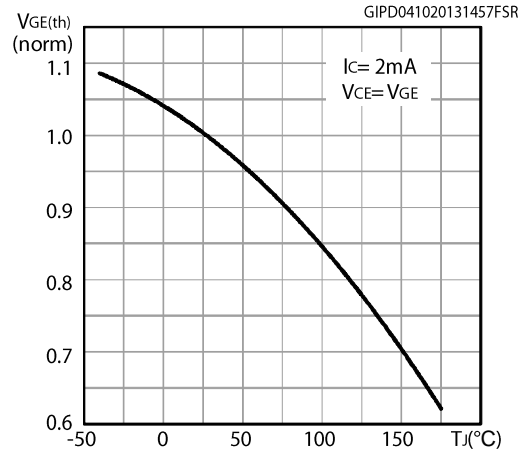


Figure 12: Normalized V(BR)CES vs. junction temperature

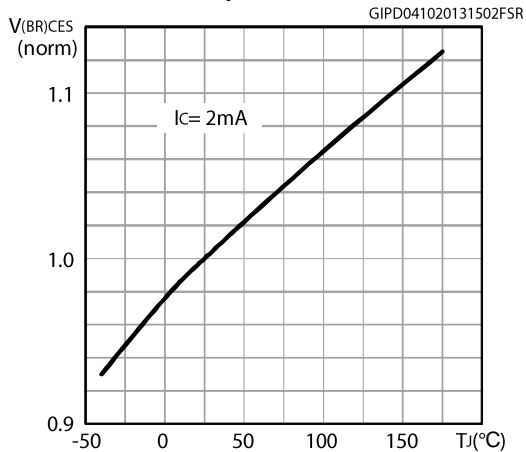
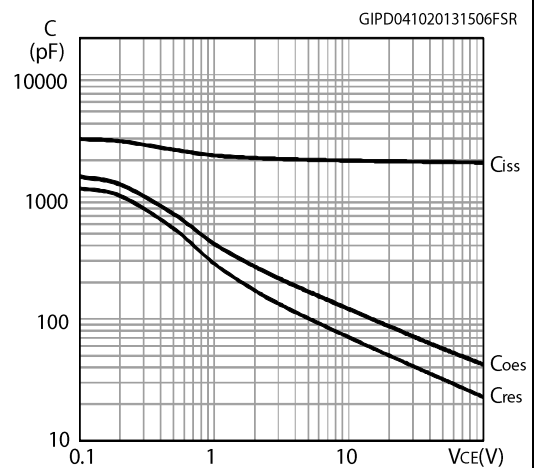
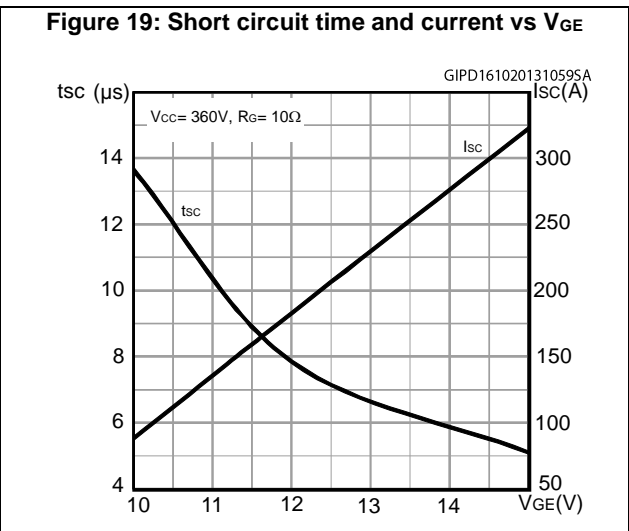
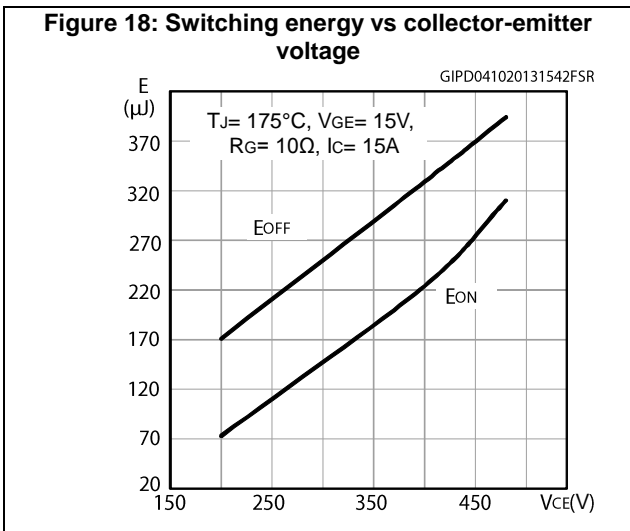
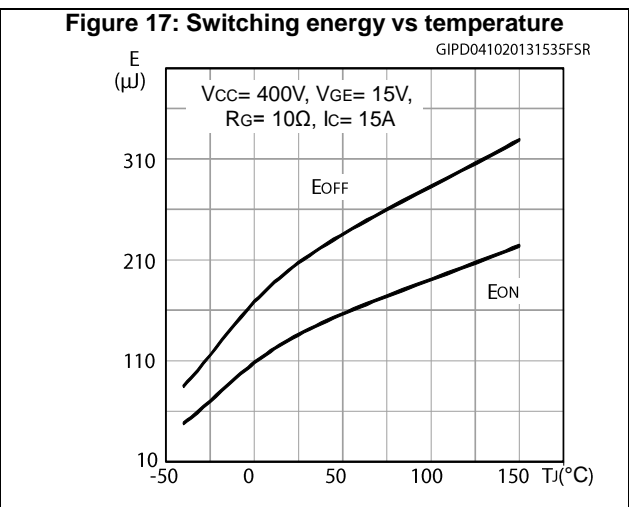
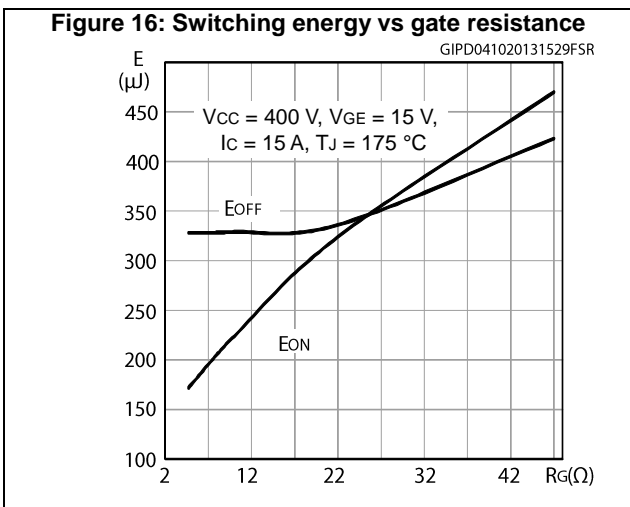
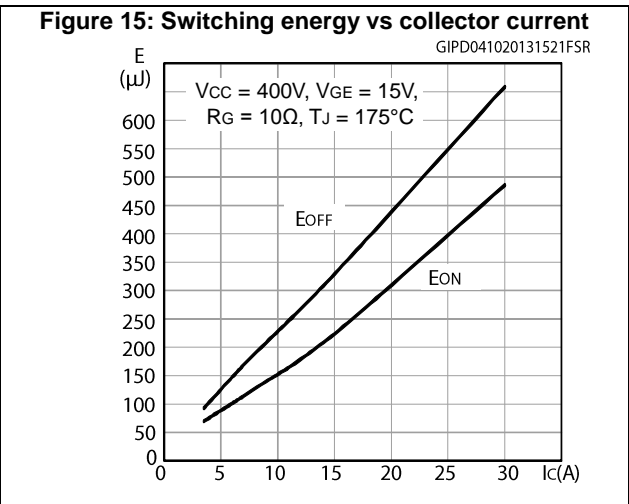
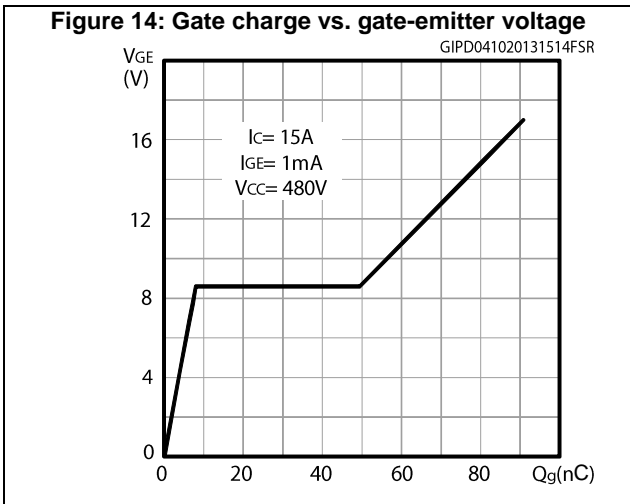
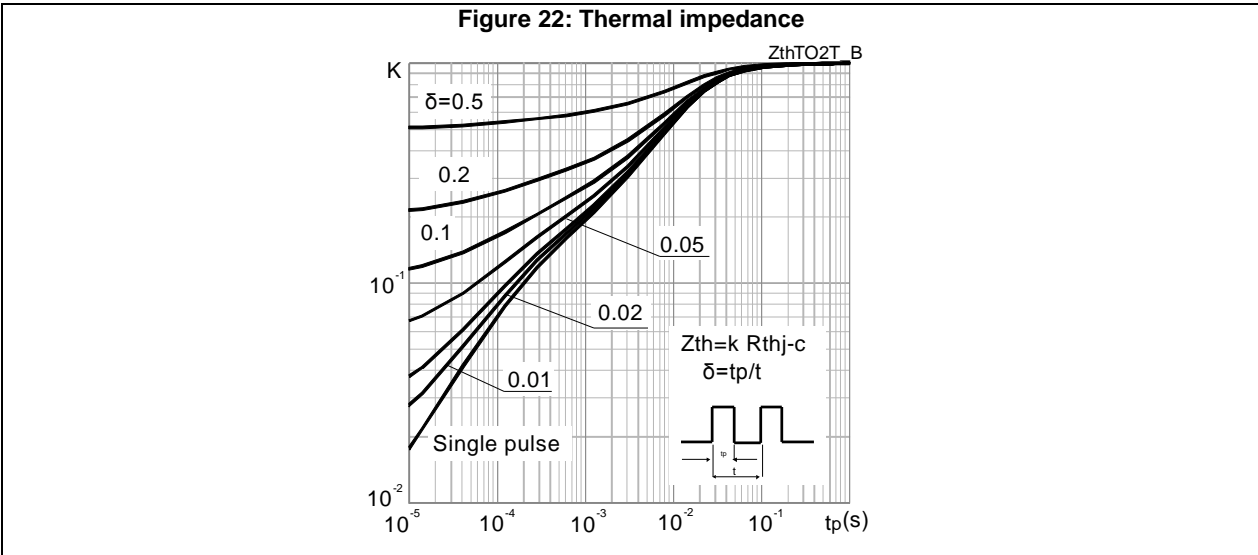
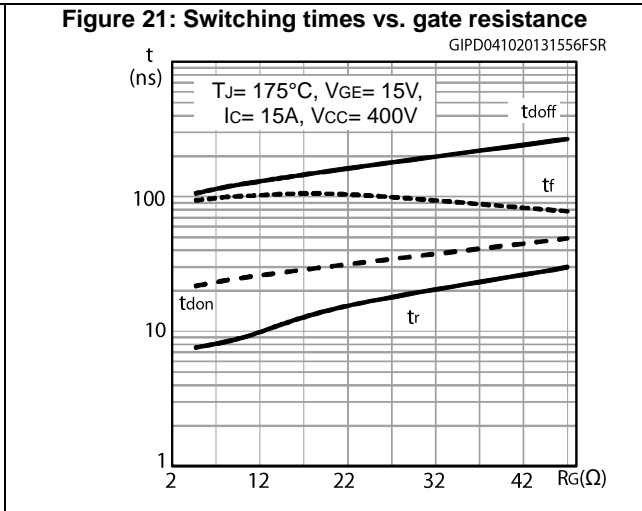
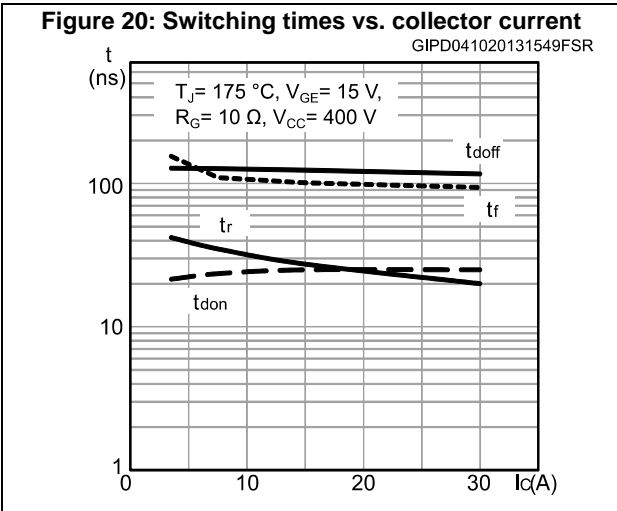


Figure 13: Capacitance variation



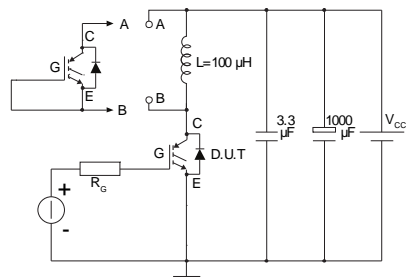






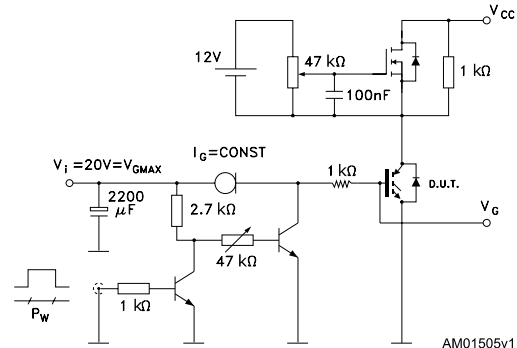
### 3 Test circuits

**Figure 23: Test circuit for inductive load switching**



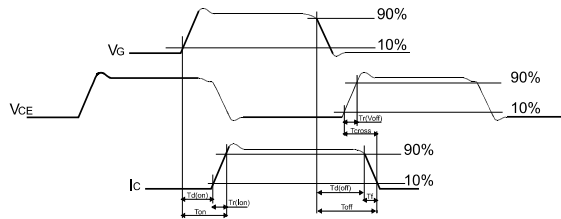
AM01504v1

**Figure 24: Gate charge test circuit**



AM01505v1

**Figure 25: Switching waveform**



AM01506v1

## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO-3P package information

Figure 26: TO-3P package outline

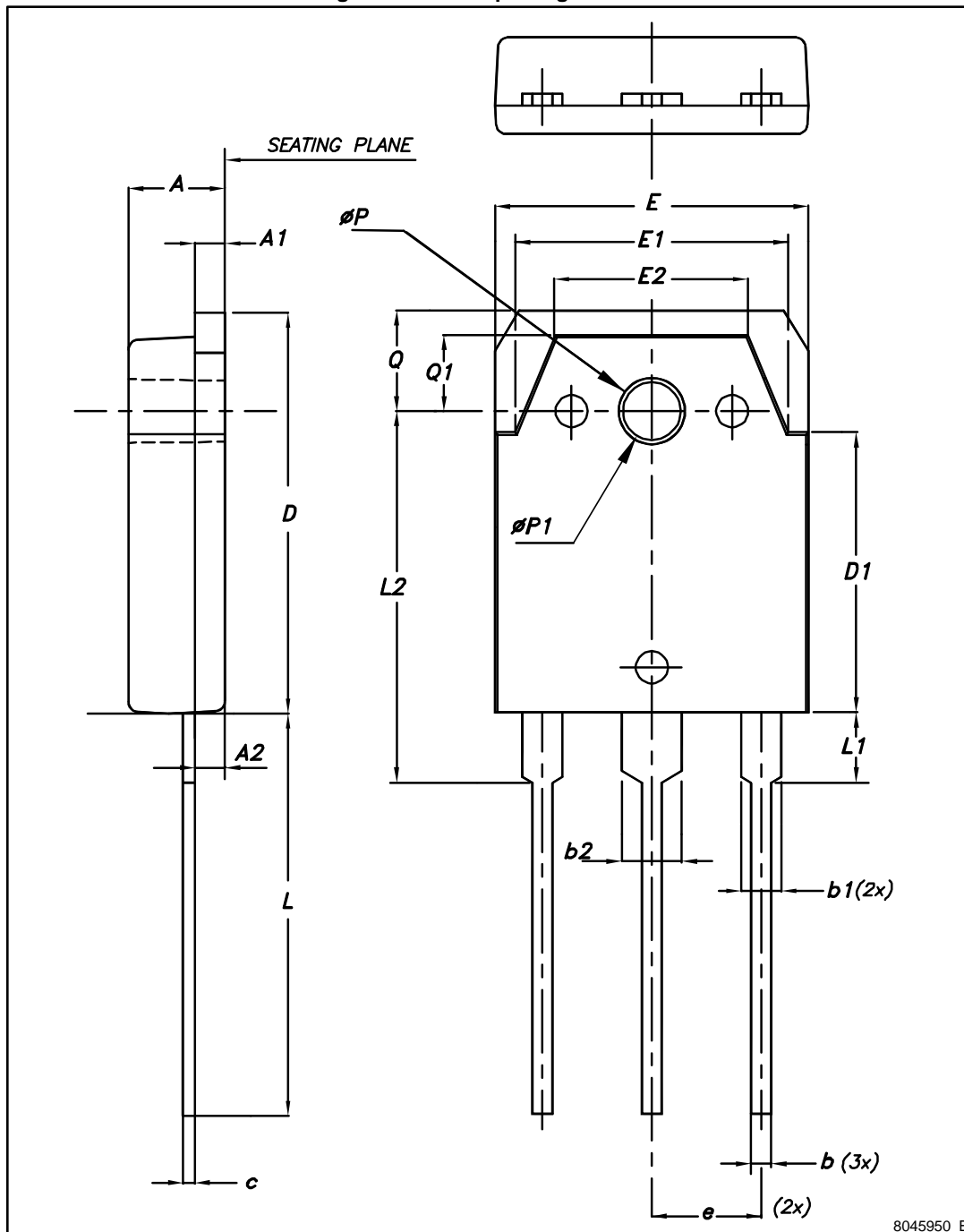


Table 8: TO-3P package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.60	4.80	5.00
A1	1.45	1.50	1.65
A2	1.20	1.40	1.60
b	0.80	1.00	1.20
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.55	0.60	0.75
D	19.70	19.90	20.10
D1	13.70	13.90	14.10
E	15.40	15.60	15.80
E1	13.40	13.60	13.80
E2	9.40	9.60	9.90
e	5.15	5.45	5.75
L	19.80	20.00	20.20
L1	3.30	3.50	3.70
L2	18.20	18.40	18.60
ØP	3.30	3.40	3.50
ØP1	3.10	3.20	3.30
Q	4.80	5.00	5.20
Q1	3.60	3.80	4

## 5 Revision history

Table 9: Document revision history

Date	Revision	Changes
10-Feb-2017	1	First release

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